## Atty. Docket No.: 1100.1114101 (H16-26549) Applicant: Robert A. Morgan et al. Applicant: Robert A. Morgan et al. Applicant: Robert A. Morgan et al. Filing Date Group Art: December 29, 2000 2872

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<b>VQ</b>	RADEMARK		U.S. PATENT DOCUMENTS		<del>)</del>		
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	AB	4,466,694	08/21/1984	MacDonald	385	37	
	AC	4,660,207	04/21/1987	Svilans	372	45	
	AD	4,784,722	11/15/1988	Liau et al.	156	649	
	AE	4,885,592	12/05/1989	Kofol et al.	343	753	
	AF	4,901,327	02/13/1990	Bradley	372	45	
	AG_	4,943,970	07/24/1990	Bradley	372	45	l
	AH	4,956,844	09/11/1990	Goodhue et al.	372	44	
	ΑI	5,031,187	07/09/1991	Orenstein et al.	372	50	 
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	AK	5,056,098	10/08/1991	Anthony et al.	372	45	
	AL	5,062,115	10/29/1991	Thornton	372	50	
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	AQ	5,216,263	06/01/1993	Paoli	257	88	
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BV	5,642,376	06/24/1997	Olbright et al.	372	45	
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BZ	5,818,066	10/06/1998	Duboz	257	21	
	5,903,590	05/11/1999	Hadley et al.	372	96	
CA	5,940,422	08/17/1999	Johnson	372	45	
CB CC	5,978,401	11/02/1999	Morgan	372	50	
CD	6,055,262	04/25/2000	Cox et al.	372	96	

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OU	(a.	E-PATENTS AND PUBLICATIONS FOR	Applicant: Robert A. Morgan et al.		
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